

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics ²⁾						
Thermal resistance, junction - case	R_{thJC}	-	-	-	1.1	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	-	62	
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm ² cooling area ³⁾	-	-	40	

Electrical characteristics, at $T_j=25^\circ\text{C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-1mA$	-40	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-340\mu A$	-1.2	-1.7	-2.2	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=-32V, V_{GS}=0V, T_j=25^\circ\text{C}$	-	-0.05	-1	μA
		$V_{DS}=-32V, V_{GS}=0V, T_j=125^\circ\text{C}^{2)}$	-	-20	-200	
Gate-source leakage current	I_{GSS}	$V_{GS}=-16V, V_{DS}=0V$	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-100A$	-	4.0	5.2	m Ω
		$V_{GS}=-4.5V, I_D=-100A, \text{SMD version}$	-	3.7	4.9	
		$V_{GS}=-10V, I_D=-100A$	-	2.9	3.4	
		$V_{GS}=-10V, I_D=-100A, \text{SMD version}$	-	2.6	3.1	

Parameter	Symbol	Conditions	Values			Unit
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Dynamic characteristics²⁾

Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=-25V,$ $f=1MHz$	-	11380	15000	pF
Output capacitance	C_{oss}		-	3410	5000	
Reverse transfer capacitance	C_{rss}		-	135	270	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-20V,$ $V_{GS}=-10V, I_D=-120A,$ $R_G=3.5\Omega$	-	21	-	ns
Rise time	t_r		-	16	-	
Turn-off delay time	$t_{d(off)}$		-	85	-	
Fall time	t_f		-	57	-	

Gate Charge Characteristics²⁾

Gate to source charge	Q_{gs}	$V_{DD}=-32V,$ $I_D=-120A,$ $V_{GS}=0 \text{ to } -10V$	-	40	52	nC
Gate to drain charge	Q_{gd}		-	32	64	
Gate charge total	Q_g		-	180	234	
Gate plateau voltage	$V_{plateau}$		-	3.5	-	V

Reverse Diode

Diode continuous forward current ²⁾	I_S	$T_C=25^\circ C$	-	-	-120	A
Diode pulse current ²⁾	$I_{S,pulse}$		-	-	-480	
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_F=-100A,$ $T_j=25^\circ C$	-	-1	-1.3	V
Reverse recovery time ²⁾	t_{rr}	$V_R=-20V, I_F=-50A,$ $di_F/dt=-100A/\mu s$	-	54		ns
Reverse recovery charge ²⁾	Q_{rr}		-	60		nC

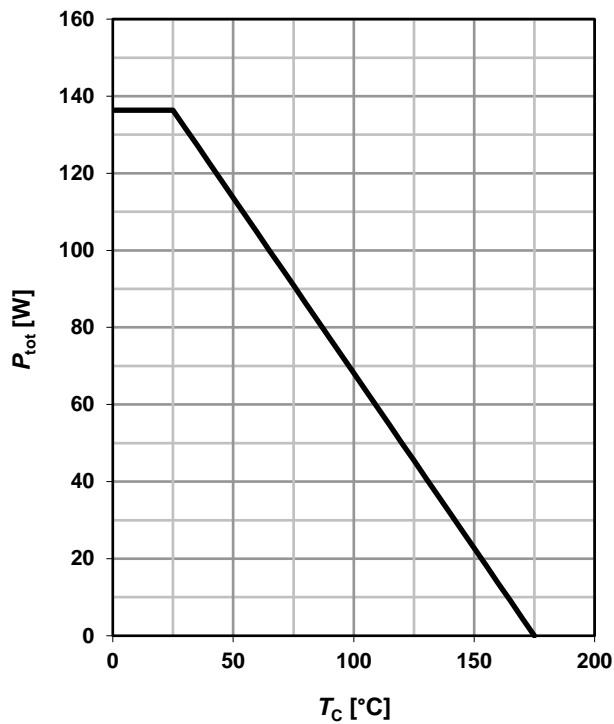
¹⁾ Current is limited by bondwire; with an $R_{thJC} = 1.1K/W$ the chip is able to carry -171A at 25°C.

²⁾ Defined by design. Not subject to production test.

³⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

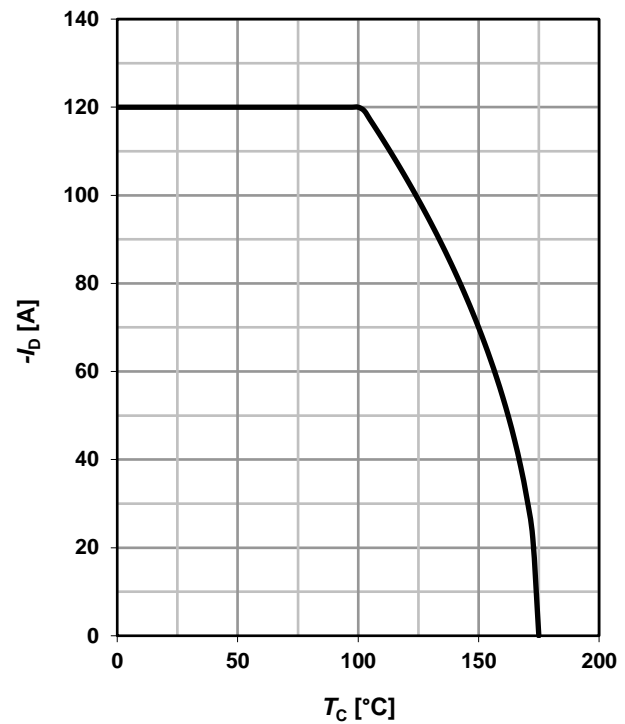
1 Power dissipation

$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \leq -6\text{V}$$



2 Drain current

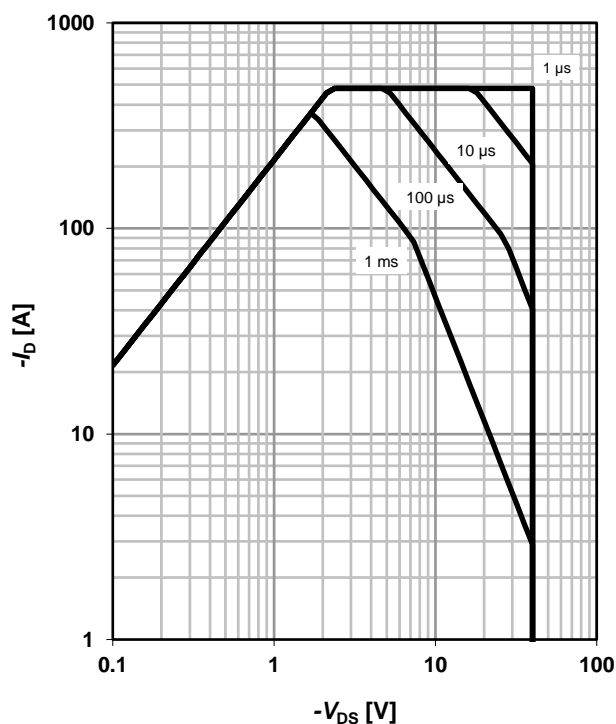
$$I_D = f(T_C); V_{\text{GS}} \leq -6\text{V}; \text{SMD}$$



3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25\text{ °C}; D = 0; \text{SMD}$$

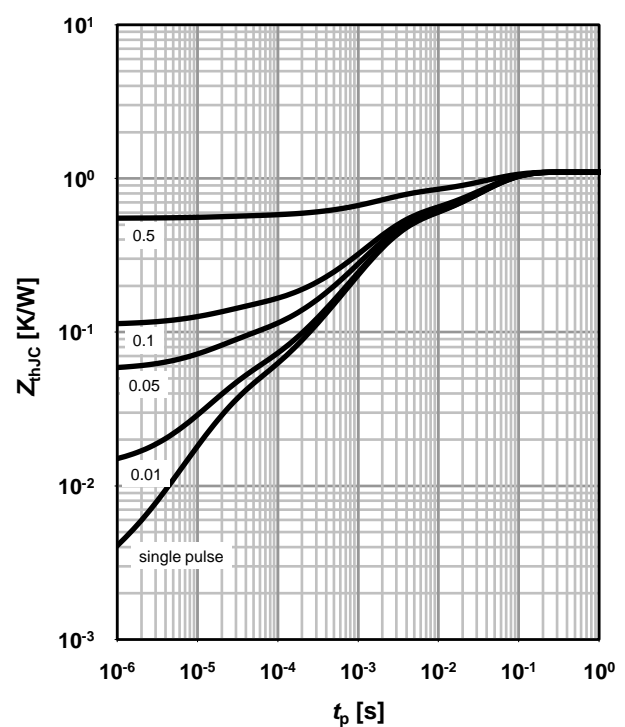
parameter: t_p



4 Max. transient thermal impedance

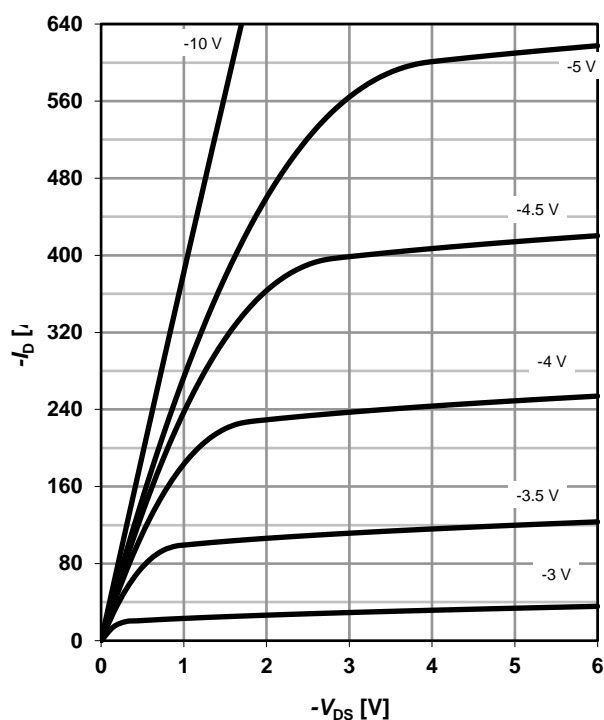
$$Z_{\text{thJC}} = f(t_p)$$

parameter: $D = t_p/T$



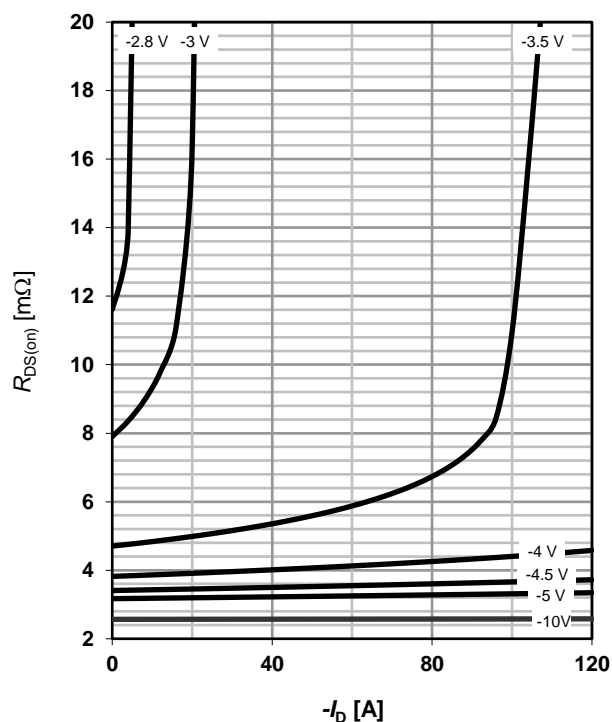
5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}; \text{SMD}$

parameter: V_{GS}


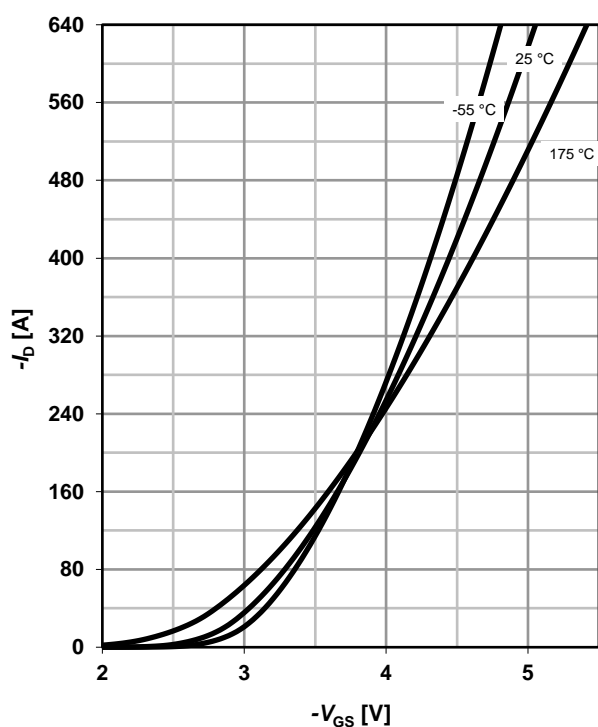
6 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}; \text{SMD}$

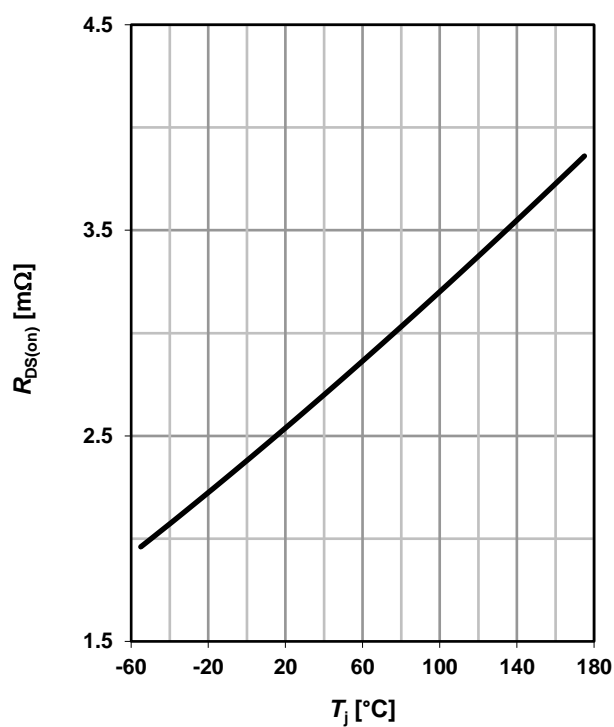
parameter: V_{GS}


7 Typ. transfer characteristics

 $I_D = f(V_{GS}); V_{DS} = -6\text{V}$

parameter: T_j


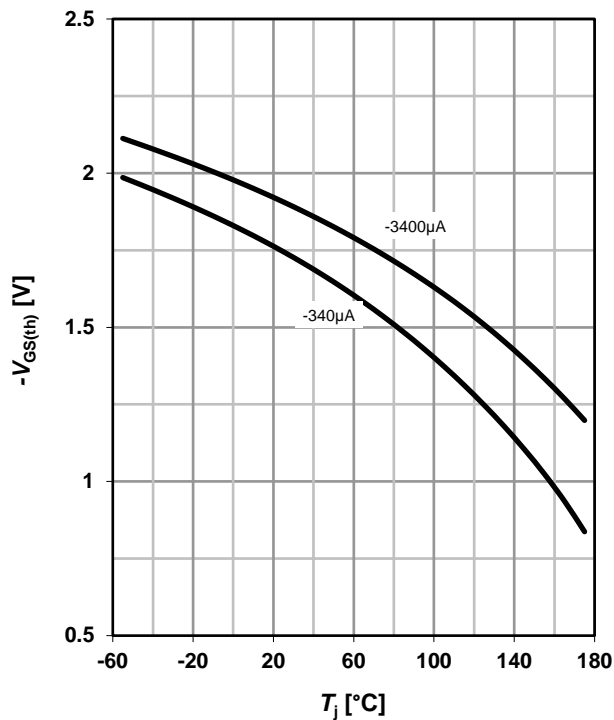
8 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(T_j); I_D = -100\text{ A}; V_{GS} = -10\text{ V}; \text{SMD}$


9 Typ. gate threshold voltage

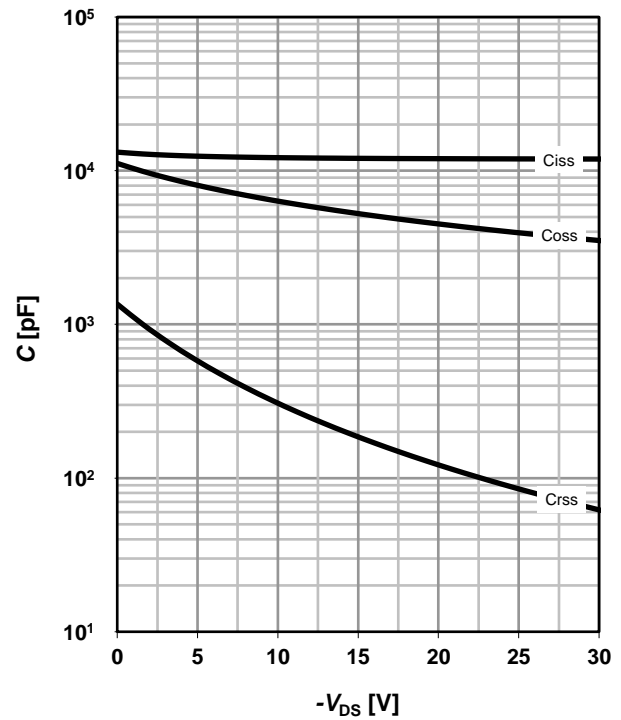
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter: I_D



10 Typ. capacitances

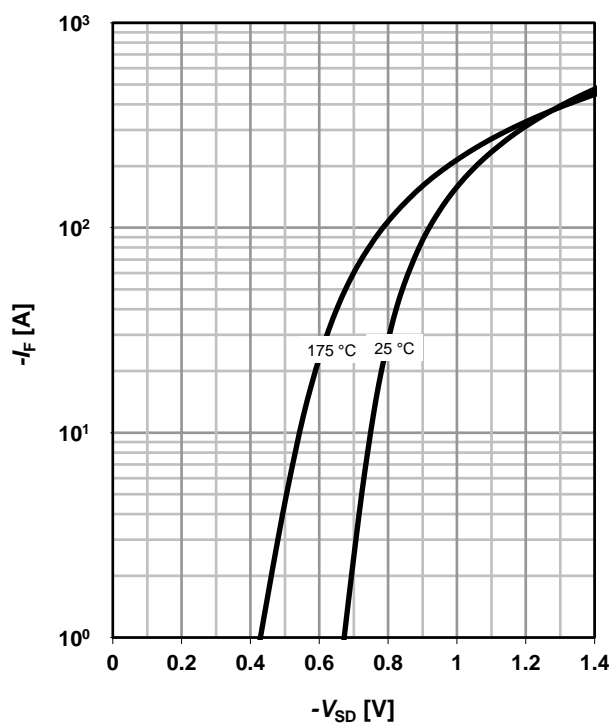
$$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$$



11 Typical forward diode characteristics

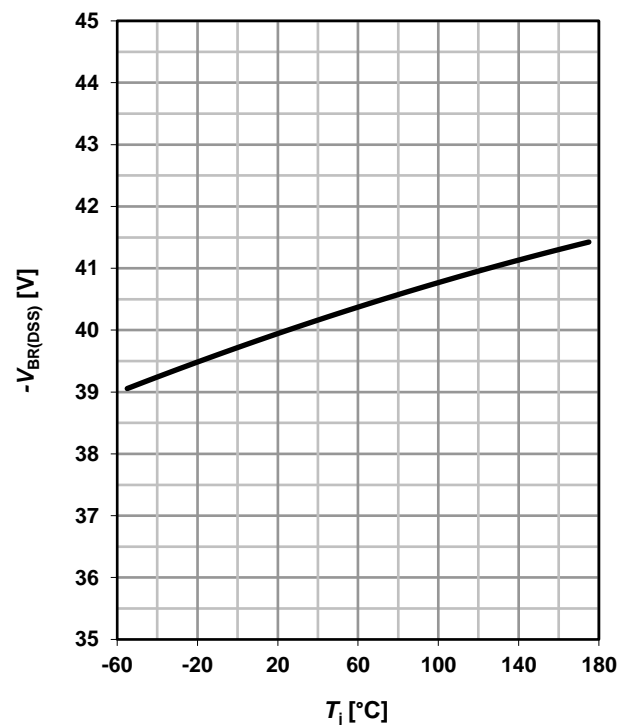
$$I_F = f(V_{SD})$$

parameter: T_j



12 Drain-source breakdown voltage

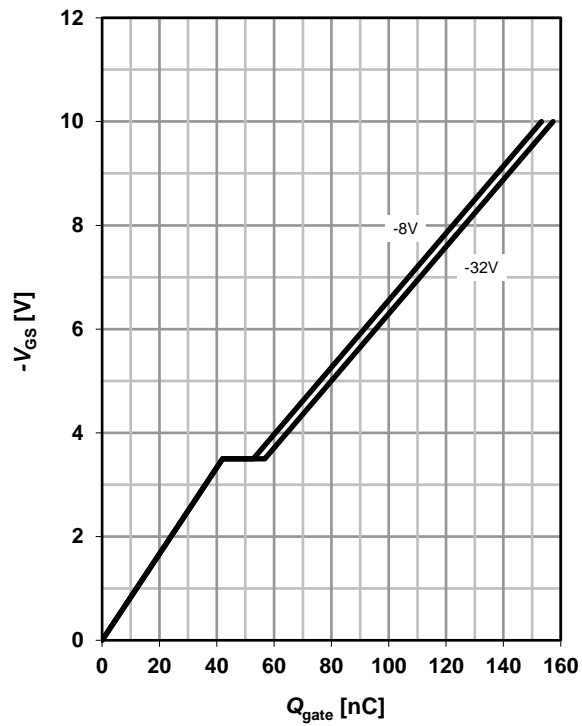
$$V_{BR(DSS)} = f(T_j); I_D = -1 mA$$



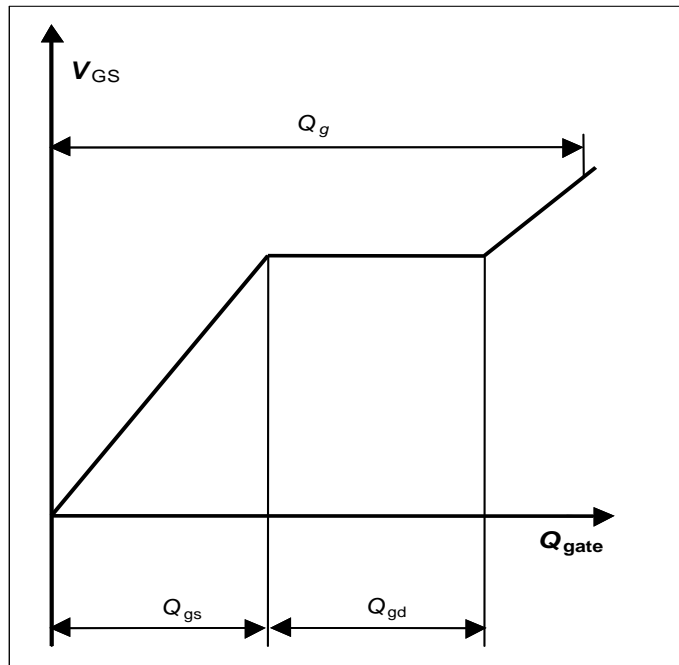
13 Typ. gate charge

$V_{GS} = f(Q_{gate}); I_D = -120 \text{ A pulsed}$

parameter: V_{DD}



14 Gate charge waveforms



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Revision History

Version	Date	Changes
1.0	24.01.2011	Final Data Sheet
1.1	27.05.2015	Update of marking
1.2	03.07.2019	V _{GS} changed